

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

107317-00039

SERIAL NO.

Div. of 08/787,451

LIST OF REFERENCES CITED BY APPLICANT

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HASHIMOTO et al.

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10/028429
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EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
K.N.	AA	4,563,367	1/7/86	SHERMAN	156	643	
K.N.	AB	4,564,997	1/21/86	MATSUO ET AL.	156	647	
K.N.	AC	5,016,564	5/21/91	NAKAMURA ET AL.	156	345	
K.N.	AD	4,960,073	10/2/90	SUZUKI ET AL.	156	345	
K.N.	AE	5,022,977	6/11/91	MATSUOKA ET AL.			
K.N.	AF	5,259,922	11/9/93	YAMMNO ET AL.	156	643	

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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO PART.		
K.N.	AG	5-90224	4/9/93	JAPAN					
K.N.	AH	60/117723	6/25/85	JAPAN					
K.N.	AI	4-340717	11/27/92	JAPAN					
K.N.	AJ	2-94628	4/5/90	JAPAN	156	345			
K.N.	AK	1-14920	1/19/89	JAPAN	156	345			
K.N.	AL	1-32631	2/2/89	JAPAN	156	345			

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	AM	N. Jiwari et al., Japan J. Appl. Phys. 32(6b) 3019 "Al etching...helicon wave plasma", 6/1993.
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K.N.	AO	M.W. Horn et al., Optical Eng. 32(10) 2388 "Comparison of etching tools...", 10/1993.

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12/5/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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K.N.	AA	5,344,536	9/6/94	OBUCHI et al..	156	643	
K.N.	AB	5,156,703	10/20/92	OECHSNER	156	643	
K.N.	AC	5,183,777	2/2/93	DORI et al.	437	225	
K.N.	AD	5,444,207	8/22/95	SEKINE et al.	204	298	
K.N.	AE	5,290,382	3/1/94	ZAROWIN et al.	204	298	
K.N.	AF	4,298,419	11/3/81	SUZUKI et al.	216	70	

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K.N.	AG	04-354124	12/8/92	JAPAN					
K.N.	AH	5-234955	9/10/93	JAPAN	216	70			
K.N.	AI	63-43324	2/24/88	JAPAN	156	345			
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K.N.	AO	M. Shimada et al., J. Vac. Sci. Technol. A 11(11), July/August 1993, pg. 1313, "Compact ECR ion source with a permanent magnet".

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K.N.	AA	5,368,685	11/29/94	KUMIHASHI et al.	216	70	
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K.N.	AM	K. Junck et al., J. Vac. Sci. Technol. A12(3), May/June 1994, pg760, "ECR plasmas in 3 magnetic field configurations"
K.N.	AN	V. Hashimoto, Japan J. Appl. Phys., 32 (1993) 6109, "Charge Damage in Plasma Etching...through Antenna".
K.N.	AO	S. Samukawa et al., J. Vac Sci. Technol, B93 (1991) 1471 "400 KMZ RF biased ECR plasma etching for"

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K. Hennigsen

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K.N.	AM	S. Samukawa, Japan J. Appl. Phys. 30, 11B (1991) 3154 "400 KHZ RF biased ECR resonance position etching".
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K. N. Himminger

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